

ABSTRACT OF THE DISCLOSURE

[0039] The invention includes methods of forming memory circuitry. In one implementation, a semiconductor substrate includes a pair of word lines having a bit node received therebetween. A bit node contact opening is formed within insulative material over the bit node. Sacrificial plugging material is formed within the bit node contact opening between the pair of word lines. Sacrificial plugging material is removed from the bit node contact opening between the pair of word lines, and it is replaced with conductive material that is in electrical connection with the bit node. Thereafter, the conductive material is formed into a bit line.